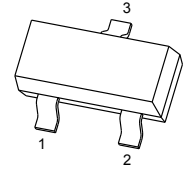


## 2N7002 MOSFET (N-Channel)

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
60V	5Ω@10V	115mA
	7Ω@5V	

### SOT-23

1. GATE
2. SOURCE
3. DRAIN



### FEATURE

High density cell design for low  $R_{DS(ON)}$

Voltage controlled small signal switch

Rugged and reliable

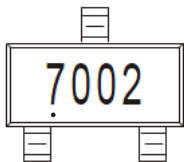
High saturation current capability

### APPLICATION

Load Switch for Portable Devices

DC/DC Converter

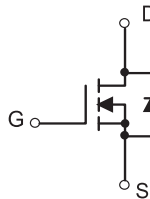
### MARKING



7002=Device code

Solid dot = Green molding compound device, if none, the normal device

### Equivalent Circuit



### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current	$I_D$	0.115	A
Power Dissipation	$P_D$	0.225	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-50 ~+150	

## MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25\text{ }^\circ\text{C}$  unless otherwise specified

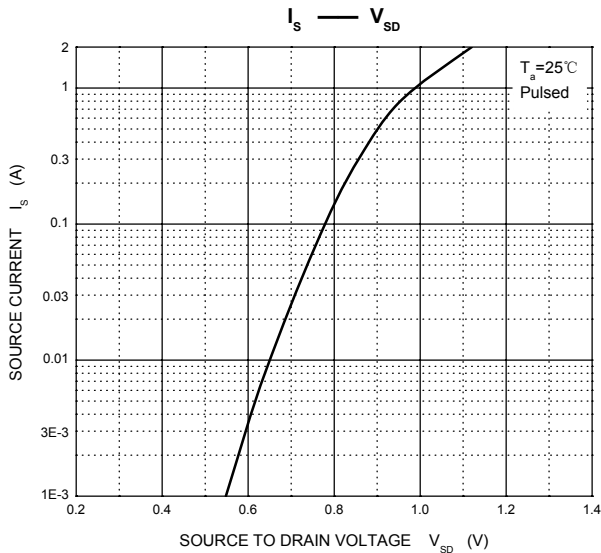
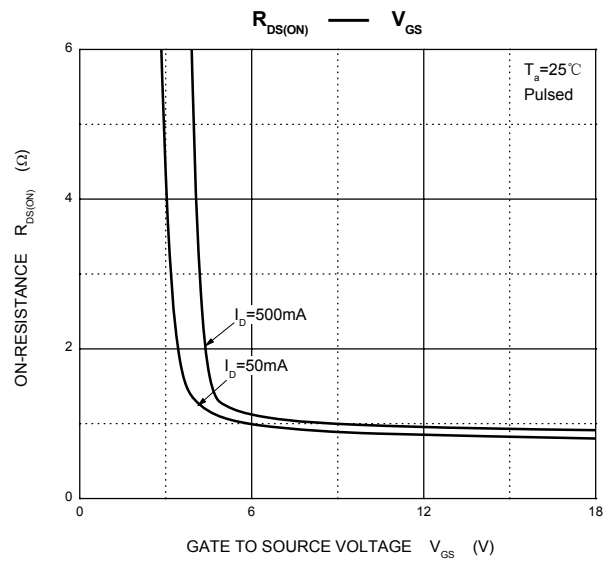
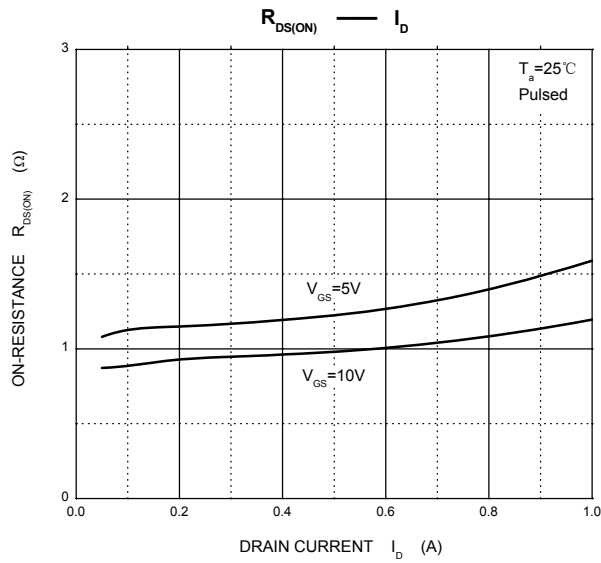
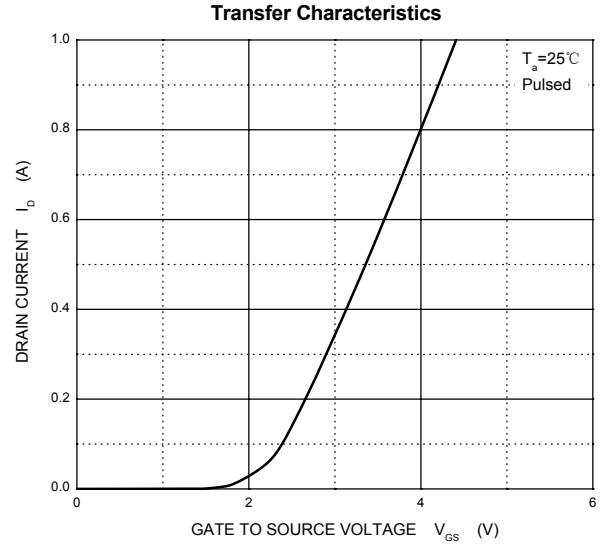
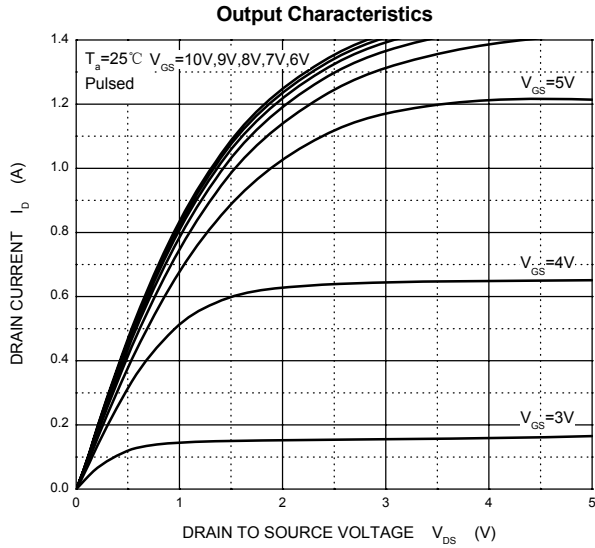
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	60			V
Gate-Threshold Voltage	$V_{th(GS)}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	1	1.6	2.5	
Gate-body Leakage	$I_{GSS}$	$V_{DS}=0\text{ V}, V_{GS}=\pm 20\text{ V}$			$\pm 80$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60\text{ V}, V_{GS}=0\text{ V}$			80	nA
On-state Drain Current	$I_{D(ON)}$	$V_{GS}=10\text{ V}, V_{DS}=7\text{ V}$	500			mA
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=500\text{mA}$		0.9	5	$\Omega$
		$V_{GS}=5\text{ V}, I_D=50\text{mA}$		1.1	7	
Forward Trans conductance	$g_{fs}$	$V_{DS}=10\text{ V}, I_D=200\text{mA}$	80			ms
Drain-source on-voltage	$V_{DS(on)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$			3.75	V
		$V_{GS}=5\text{V}, I_D=50\text{mA}$			0.375	V
Diode Forward Voltage	$V_{SD}$	$I_S=115\text{mA}, V_{GS}=0\text{ V}$	0.55		1.2	V
Input Capacitance *	$C_{iss}$	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$			50	pF
Output Capacitance *	$C_{oss}$				25	
Reverse Transfer Capacitance *	$C_{rss}$				5	

### SWITCHING TIME

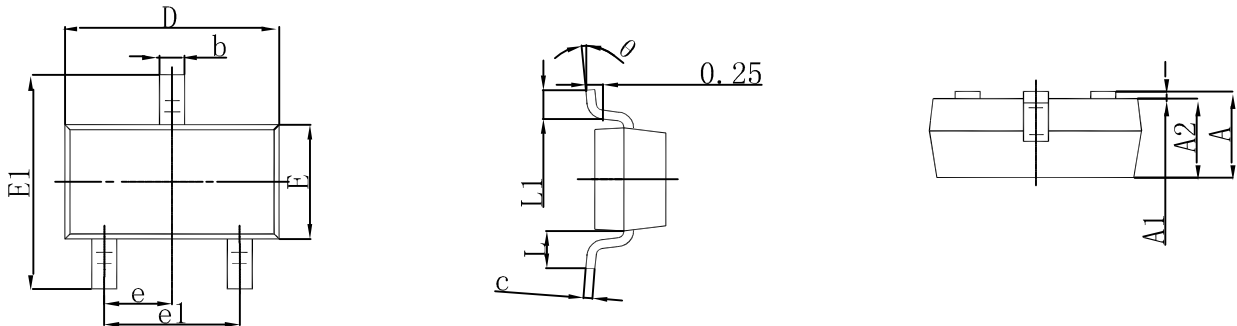
Turn-on Time *	$t_{d(on)}$	$V_{DD}=25\text{ V}, R_L=50\Omega,$ $I_D=500\text{mA}, V_{GEN}=10\text{ V}$			20	ns
Turn-off Time*	$t_{d(off)}$		$R_G=25\Omega$			

\*These parameters have no way to verify.

## Typical Characteristics

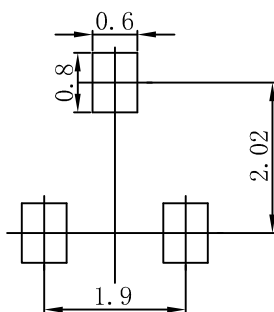


## SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## SOT-23 Suggested Pad Layout



**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.